



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



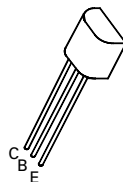
# PNP SILICON PLANAR MEDIUM POWER HIGH VOLTAGE TRANSISTORS

ISSUE 2 – JULY 94

## ZTX756 ZTX757

### FEATURES

- \* 300 Volt  $V_{CEO}$
- \* 0.5 Amp continuous current
- \*  $P_{tot} = 1$  Watt



**E-Line  
TO92 Compatible**

### ABSOLUTE MAXIMUM RATINGS.

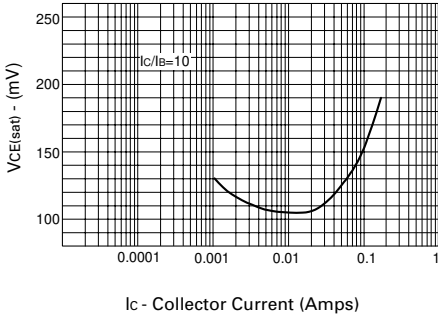
PARAMETER	SYMBOL	ZTX756	ZTX757	UNIT
Collector-Base Voltage	$V_{CBO}$	-200	-300	V
Collector-Emitter Voltage	$V_{CEO}$	-200	-300	V
Emitter-Base Voltage	$V_{EBO}$		-5	V
Peak Pulse Current	$I_{CM}$		-1	A
Continuous Collector Current	$I_C$		-0.5	A
Power Dissipation at $T_{amb}=25^{\circ}C$	$P_{tot}$		1	W
Operating and Storage Temperature Range	$T_j; T_{stg}$		-55 to +200	$^{\circ}C$

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

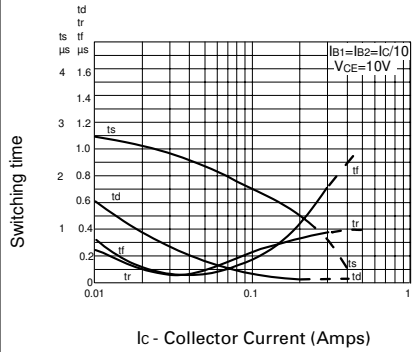
PARAMETER	SYMBOL	ZTX756		ZTX757		UNIT	CONDITIONS.
		MIN.	MAX.	MIN.	MAX.		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-200		-300		V	$I_C = -100\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-200		-300		V	$I_C = -10mA, I_B = 0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		-5		V	$I_E = -100\mu A, I_C = 0$
Collector Cut-Off Current	$I_{CBO}$		-100		-100	nA	$V_{CB} = -160V, I_E = 0$ $V_{CB} = -200V, I_E = 0$
Emitter Cut-Off Current	$I_{EBO}$		-100		-100	nA	$V_{EB} = -3V, I_C = 0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.5		-0.5	V	$I_C = -100mA, I_B = -10mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-1.0		-1.0	V	$I_C = -100mA, I_B = -10mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-1.0		-1.0	V	$I_C = -100mA, V_{CE} = -5V^*$
Static Forward Current Transfer Ratio	$h_{FE}$	50 40		50 40			$I_C = -100mA, V_{CE} = -5V^*$ $I_C = -10mA, V_{CE} = -5V^*$
Transition Frequency	$f_T$	30		30		MHz	$I_C = -10mA, V_{CE} = -20V$ $f = 20MHz$
Output Capacitance	$C_{obo}$		20		20	pF	$V_{CB} = -20V, f = 1MHz$

# ZTX756 ZTX757

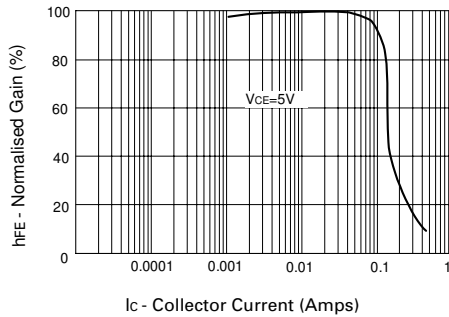
## TYPICAL CHARACTERISTICS



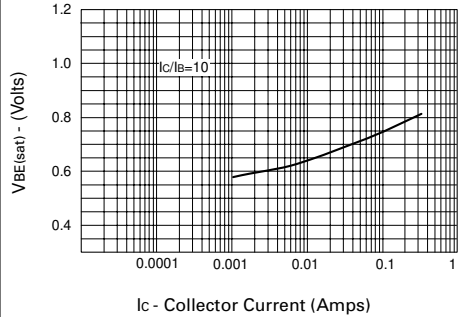
**$V_{CE(sat)}$  v  $I_C$**



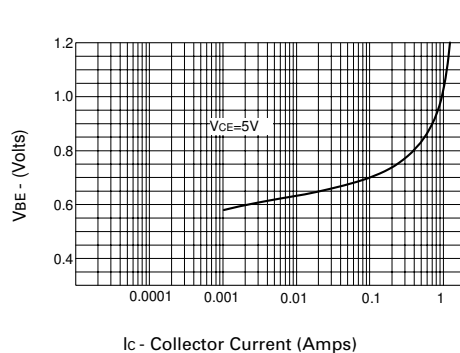
**Switching Speeds**



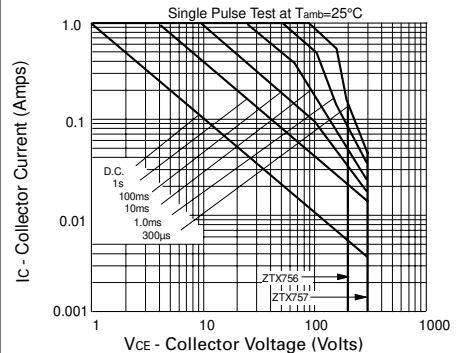
**$h_{FE}$  v  $I_C$**



**$V_{BE(sat)}$  v  $I_C$**



**$V_{BE(on)}$  v  $I_C$**



**Safe Operating Area**